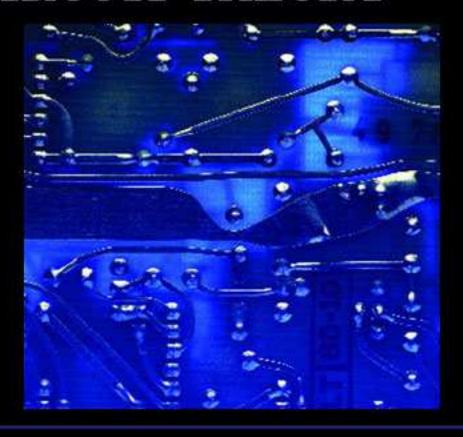
ELECTRONIC DEVICES AND CIRCUIT THEORY

TENTH EDITION

BOYLESTAD





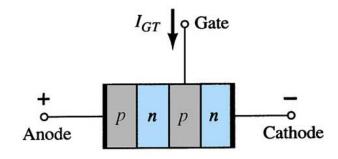
Chapter 17 pnpn and Other Devices

© Modified by Yuttapong Jiraraksopakun ENE, KMUTT 2009

SCR—Silicon-Controlled Rectifier

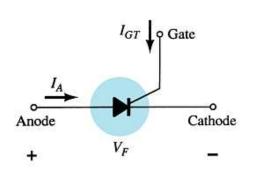
The SCR is a switching device for high-voltage and high-current operations.

Like an ordinary rectifier, an SCR conducts in one direction



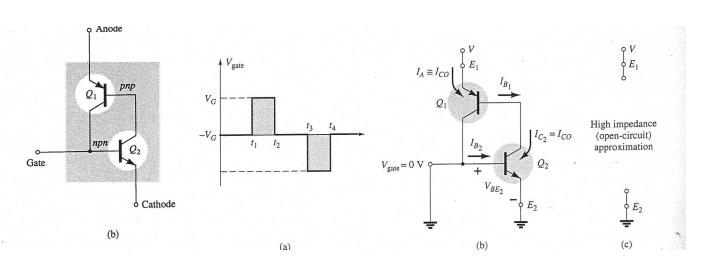
The terminals are:

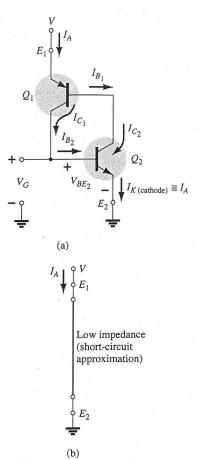
- Anode
- Cathode
- Gate





SCR—Silicon-Controlled Rectifier





SCR Operation

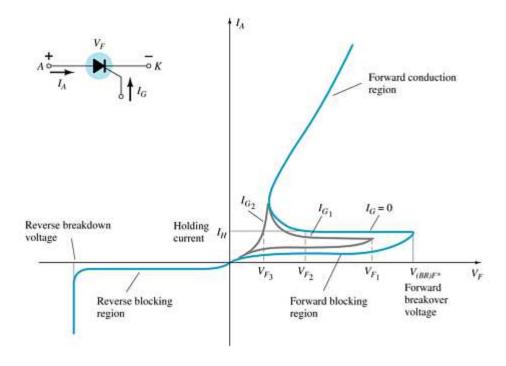
To switch on an SCR:

• Forward bias the anodecathode terminals (V_F)

AND

• Apply sufficient gate voltage (V_{gate}) and gate current (I_{GT})

Once an SCR is switched on, it remains latched on, even when the gate signal is removed.



- Holding current (I_H) is the minimum required current from anode to cathode
- Reverse breakdown voltage is the maximum reverse bias voltage for the SCR

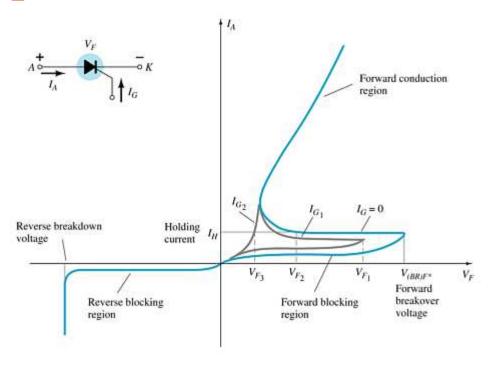
SCR Operation

To switch off an SCR:

Remove the power source the anode and cathode terminals

OR

Reverse bias the anode and cathode terminals



An SCR cannot be switched off by simply removing the gate voltage.

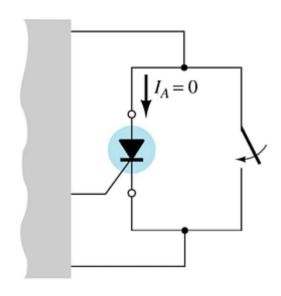
Commutation circuitry can be used for satisfying either of the conditions for switching off an SCR.

SCR Commutation

Commutation circuitry is simply a class of switching devices connected in parallel with the SCR.

A control signal activates the switching circuitry and provides a low impedance bypass for the anode to cathode current. This momentary loss of current through the SCR turns it off.

The switching circuitry can also apply a reverse bias voltage across the SCR, which also will turn off the SCR.



SCR False Triggering

An SCR can be forced to trigger conduction under several conditions that must be avoided:

- Excessively high voltage from anode to cathode
- High frequency signal from gate to cathode
- High operating temperature

SCR Applications

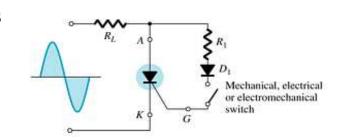
In these applications the SCR gate circuit is used to monitor a situation and trigger the SCR to turn on a portion of the circuit.

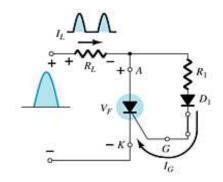
- SCR phase control
- Battery-charging regulator
- Temperature controller circuit
- Emergency-lighting system

SCR Phase Control

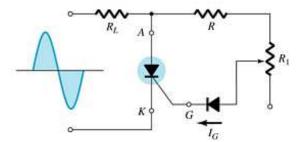
The gate voltage can be set to fire the SCR at any point in the AC cycle.

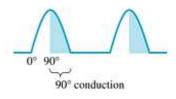
In this example, the SCR fires as soon as the AC cycle crosses 0V. Therefore it acts like a half-wave rectifier.





In this example, the SCR fires later—at the 90° point—on the positive half-cycle.





SCS—Silicon-Controlled Switch

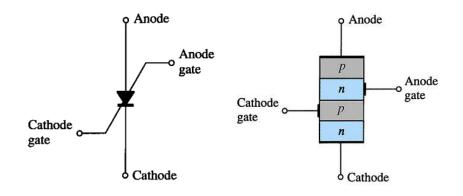
An SCS is like an SCR, except that it has two gates: a cathode gate and an anode gate.

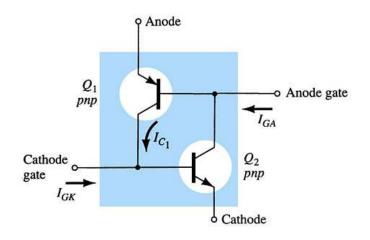
Either gate can fire the SCS

- A positive pulse or voltage on the cathode gate
- A negative pulse or voltage on the anode gate

Either gate can switch off the SCS

- A negative pulse or voltage on the Cathode gate
- A positive pulse or voltage on the anode gate





Note: The anode gate requires higher voltages than the cathode gate.

Shockley Diode

The Shockley diode conducts once the breakover voltage is reached. It only conducts in one direction.

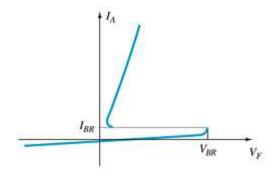
Anode + I_A Anode V_F P N Cathode Cathode

Operation

The Shockley diode must be forward biased, and then once the voltage reaches the breakover level it will conduct. Like an SCR it only conducts in one direction.

Application

Trigger switch for an SCR

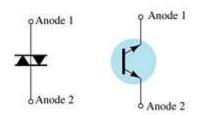


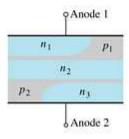
Diac

The Diac is a breakover type device.

Operation

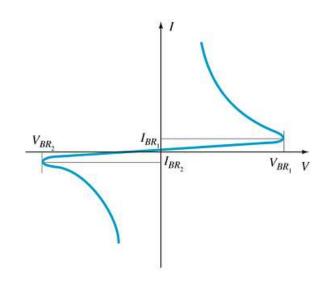
Once the breakover voltage is reached the Diac conducts. The Diac, though, can conduct in both directions. The breakover voltage is approximately symmetrical for a positive and a negative breakover voltage.





Applications

- Trigger circuit for the Triac
- Proximity sensor circuit



Triac

A triac is like a diac with a gate terminal.

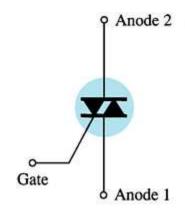
Operation

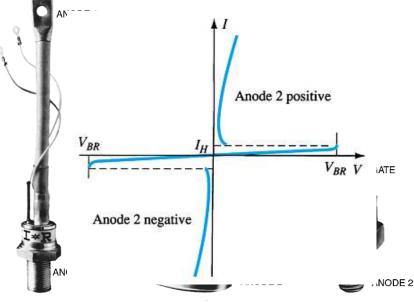
When fired by the gate or by exceeding the breakover voltage, a triac conducts in both directions.

Applications

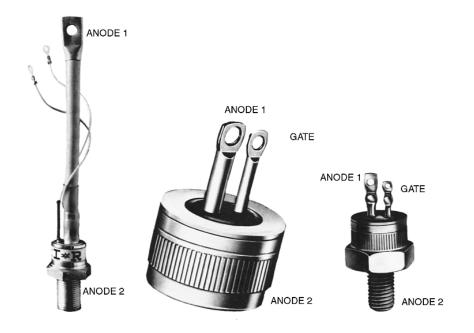
AC power control circuits

Terminal Identification





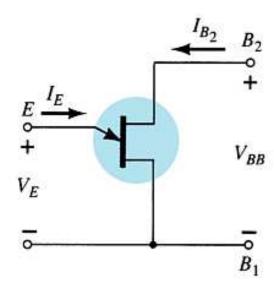
Triac Terminal Identification



The Unijunction Transistor (UJT)

The unijunction transistor (UJT) has two base terminals (B_1 and B_2) and an emitter terminal (E).

The UJT symbol resembles the FET symbol. The emitter terminal is angled as shown.



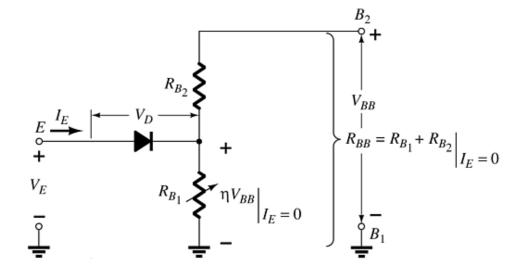
UJT Equivalent Circuit

The interbase resistance (R_{BB}) is the total resistance between the two base terminals when $I_E = 0$ A.

The intrinsic standoff ratio (η) is the ratio of R_{B1} to R_{BB} when $I_E = 0$ A.

Conduction through the emitter terminal begins when the emitter voltage reaches the firing potential, given as

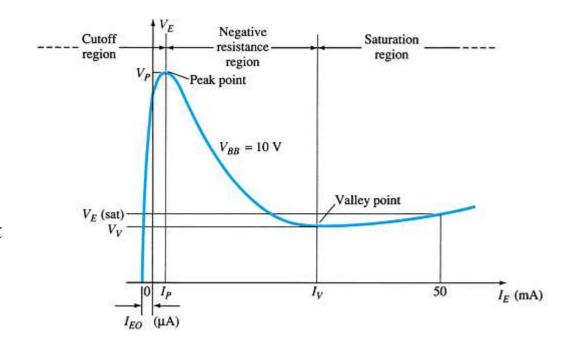
$$V_P = \eta V_{BB} + V_D$$



UJT Negative Resistance Region

After a UJT fires, emitter voltage decreases as emitter current increases.

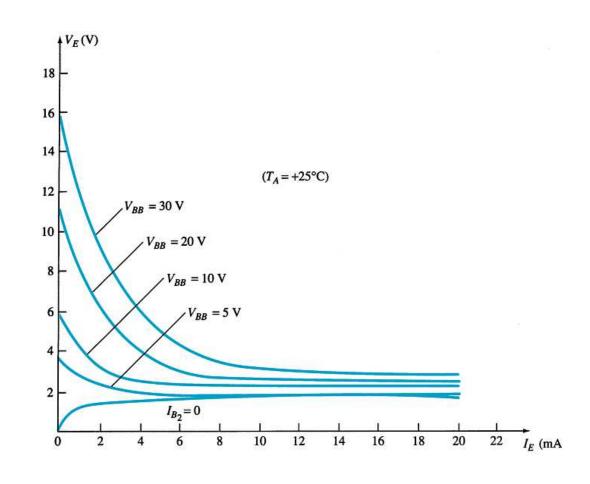
The negative resistance region of operation is definced by the peak point (V_P) and the valley point (V_V) .



UJT Emitter Curves

The UJT emitter curves show the effect of V_{BB} on UJT firing voltage (V_P) .

The higher the value of V_{BB} , the higher the value of (V_P) required to fire the component.

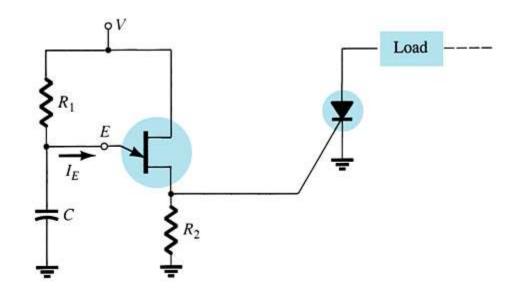


Using a UJT to trigger an SCR

The UJT is commonly used as a triggering device for other breakover devices, like the SCR.

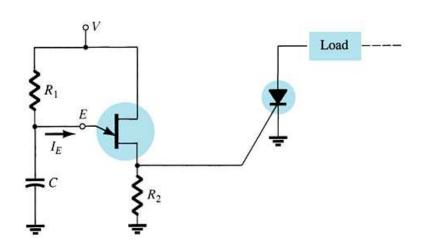
The SCR shown is triggered when the UJT emitter circuit conducts.

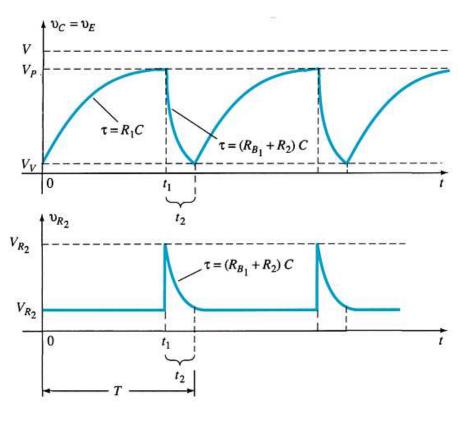
As the capacitor charges, V_E increases. When it reaches V_P , the UJT fires. The voltage developed across R_2 triggers the SCR.



Using a UJT to trigger an SCR

The V_E and V_{R2} waveforms for the SCR triggering circuit (below) are shown.



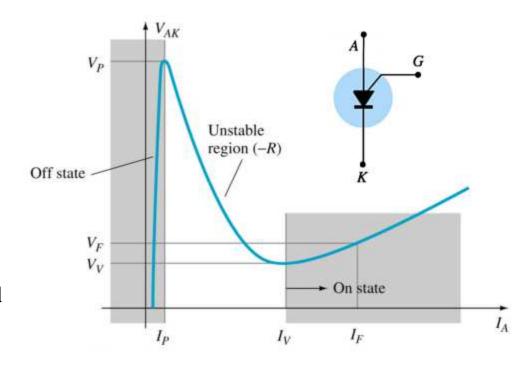


PUT—Programmable UJT

Characteristics

In some of its operating characteristics, a PUT is more like an SCR.

Like the UJT, the PUT has a negative resistance region. But this region is unstable in the PUT. The PUT is operated between the on and off states.



PUT Firing

Reducing or removing the gate voltage dies not turn off the PUT. Instead, like an SCR, the Anode to Cathode voltage must drop sufficiently to reduce the current below a holding level.

The gate voltage required to turn the PUT on is determined by external components, and not by specifications of the device as in the η value for the UJT.

$$V_{G} = \frac{R_{B1}}{R_{B1} + R_{B2}} V_{BB} = \eta V_{BB}$$

